

Schottky barrier diode

RB495D

●Applications

Low current rectification

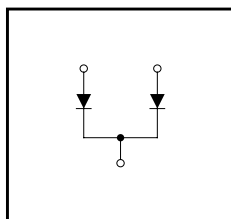
●Features

- 1) Small surface mounting type. (SMD3)
- 2) Two diodes with common cathode for excellent installation efficiency.
- 3) High reliability.

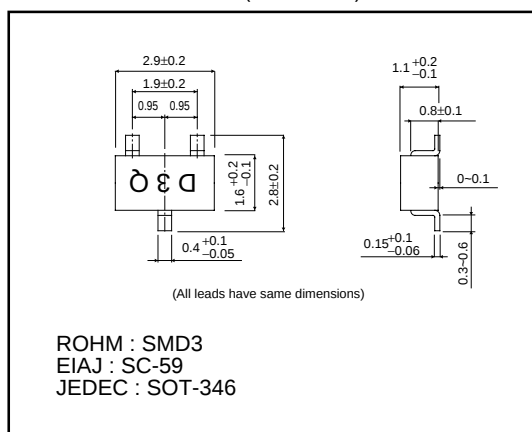
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	25	V
Mean rectifying current*1	I_o	0.4	A
Peak forward surge current*2	I_{FSM}	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C
Operating temperature	T_{opr}	-30~+85	°C

*1 Mean output current per element : $I_o / 2$

*2 60Hz for 1

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	—	0.30	V	$I_F=10mA$
	V_{F2}	—	—	0.50	V	$I_F=200mA$
Reverse current	I_R	—	—	70	μA	$V_R=25V$

Note) ESD sensitive product handling required.

Diodes

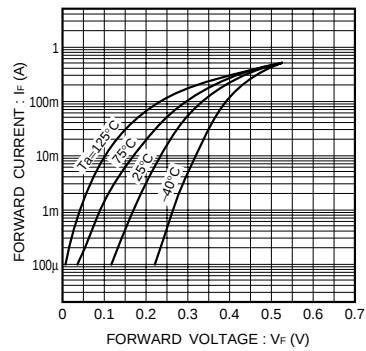
●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Forward characteristics

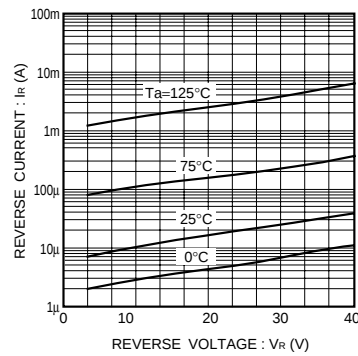


Fig.2 Reverse characteristics

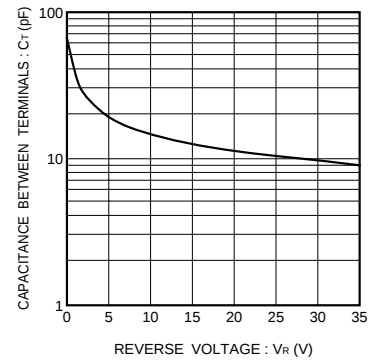


Fig.3 Capacitance between terminals characteristics